

# ABSTRACT OF THE DISCLOSURE

A pattern forming method of forming a desired pattern on a semiconductor substrate is disclosed, which comprises extracting a first pattern of a layer, extracting a second pattern of one or more layers overlapped with the layer, the second pattern being arranged close to or overlapped with the first pattern, calculating a distance between the first and second patterns on a semiconductor substrate in consideration of a predetermined process variation, determining whether or not the distance between the first and second patterns satisfy an allowable margin given for the distance between the first and second patterns, and correcting, if the distance does not satisfy the allowable margin, at least one of the first and second patterns to satisfy the allowable margin.